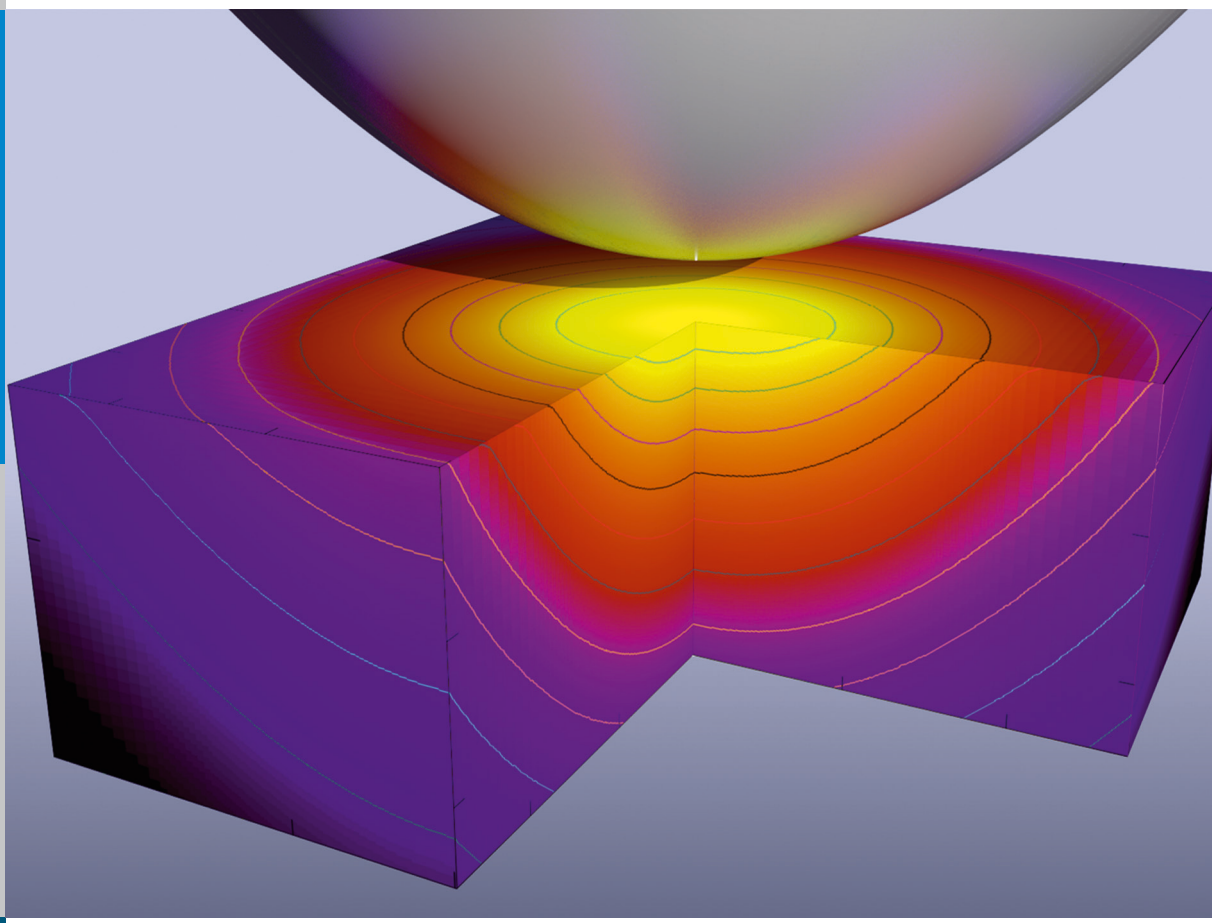
Quantitative scanning tunneling spectroscopy of non-polar III-V compound semiconductor surfaces

Michael Schnedler



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